



TS IEC 62804: draft 2013-12

Test Method for Detection of Potential Induced Degradation (PID) of Photovoltaic (PV)-Modules

Ref.: 5007790-3972-0001/198062

Applicant: Changzhou EGing Photovoltaic Technology Co., Ltd.
No. 18 Jinwu Road, 213213 Jintan City, China

Product: Crystalline silicon Photovoltaic (PV)-Modules

Type: A) EG-XXXP60-C
B) EG-XXXM60-C

XXX in the type replaces the power in watt and can be any number between:

200 – 260 for A), 200 – 265 for B)

Manufacturer: Changzhou EGing Photovoltaic Technology Co., Ltd.

Standard: TS IEC 62804: draft 2013-12, modified

Test conditions

Testing time: 96 h
Chamber temperature: 85 °C
Relative Humidity: 85 %
Potential to ground: ± 1000 V

Pass criteria

Power degradation: < 5%
Dry Insulation: > 40 M Ω m²
Wet insulation: > 40 M Ω m²





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Summary of test results:

Maximum power degradation: required max. 5 %
measured max. 1,9 %

The measured degradation is below the allowed degradation.

Dry insulation resistance: required 24,5 M Ω
measured >500 M Ω

The measured dry insulation resistance is above the limit.

Wet insulation resistance: required 24,5 M Ω
measured >500 M Ω


The measured wet insulation resistance is above the limit.

Visual inspection: No findings

The complete test results are given in Test Report No.: Report_ET2_198062.

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